TOSHIBA INSULATED GATE BIPOLAR TRANSISTOR SILICON N CHANNEL MOS TYPE

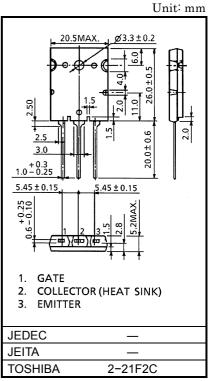
GT40M301

HIGH POWER SWITCHING APPLICATIONS

- The 3rd Generation
- FRD Included Between Emitter and Collector
- Enhancement-Mode
- High Speed IGBT : $t_f = 0.25\mu s$ (TYP.) FRD : $t_{rr} = 0.7\mu s$ (TYP.)
- Low Saturation Voltage : VCE (sat) = 3.4V (MAX.)

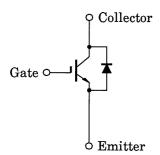
MAXIMUM RATINGS (Ta = 25°C)

| CHARACTERISTIC | | SYMBOL | RATING | UNIT | |
|--|-----|-------------------|---------|------|--|
| Collector-Emitter Voltage | | V _{CES} | 900 | V | |
| Gate-Emitter Voltage | | V _{GES} | ±25 | V | |
| Collector Current | DC | Ι _C | 40 | А | |
| | 1ms | I _{CP} | 80 | А | |
| Emitter-Collector Foward Current | DC | I _{ECF} | 15 | А | |
| | 1ms | I _{ECFP} | 120 | А | |
| Collector Power Dissipation (Tc = 25°C) | | Pc | 200 | W | |
| Junction Temperature | | Тј | 150 | °C | |
| Storage Temperature Range | | T _{stg} | -55~150 | °C | |
| Screw Torque | | _ | 0.8 | N∙m | |



Weight: 9.75g

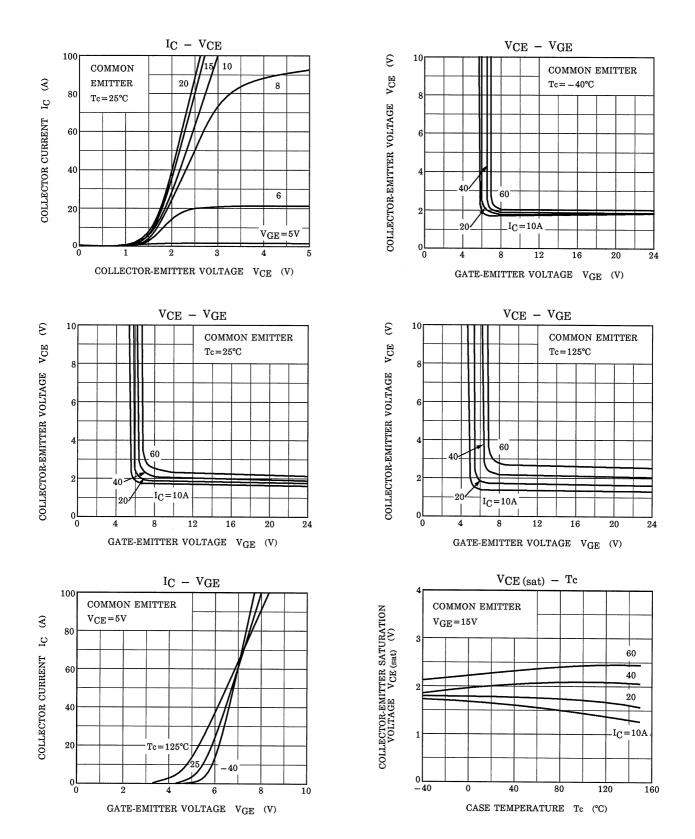
EQUIVALENT CIRCUIT



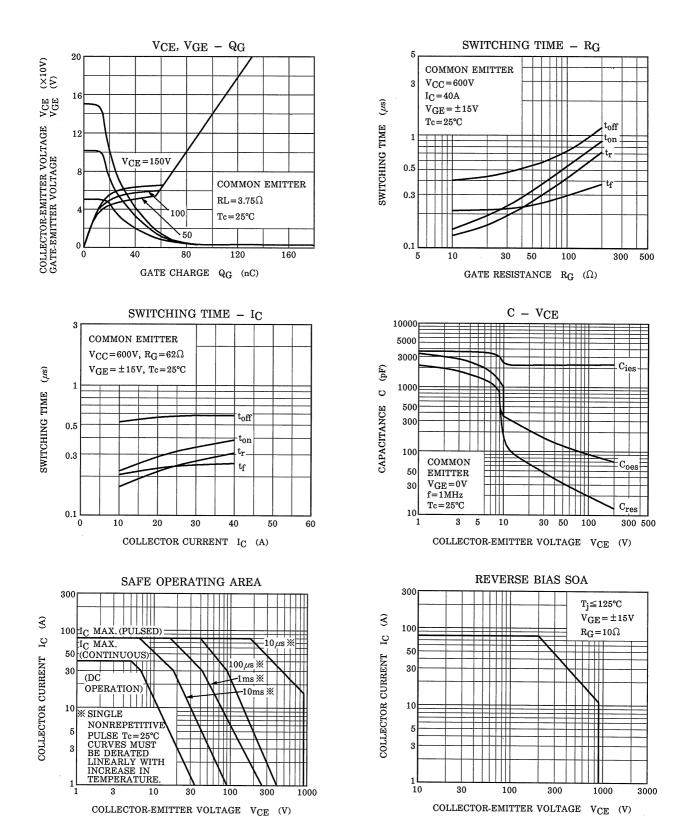
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

| CHARACTERISTIC | | SYMBOL | TEST CONDITION | MIN | TYP. | MAX | UNIT |
|--------------------------------------|---------------|---------------------------|--|-----|------|-------|------|
| Gate Leakage Current | | IGES | V _{GE} = ±25V, V _{CE} = 0 | | _ | ±500 | nA |
| Collector Cut-off Current | | ICES | V _{CE} = 900V, V _{GE} = 0 | _ | | 1.0 | mA |
| Gate-Emitter Cut-off Voltage | | V _{GE (OFF)} | I _C = 40mA, V _{CE} = 5V | 3.0 | _ | 6.0 | V |
| Collector-Emitter Saturation Voltage | | V _{CE (sat) (1)} | I _C = 8A, V _{GE} = 15V | - | 1.7 | 2.4 | V |
| Collector-Emitter Saturation Voltage | | V _{CE (sat) (2)} | I _C = 40A, V _{GE} = 15V | | 2.1 | 3.4 | V |
| Input Capacitance | | C _{ies} | V _{CE} = 30V, V _{GE} = 0 f = 1MHz | _ | 2100 | _ | pF |
| Switching Time | Rise Time | t _r | $15V_{0} \downarrow_{-15V} \downarrow_{600V} \bigcirc 0 \downarrow_{-15V} \square_{600V} \square_{60V} \bigcirc 0 \downarrow_{-15V} \square_{60V} \square_{60V} \bigcirc 0 \downarrow_{-15V} \square_{60V} \square_{60V} \square_{60V} \bigcirc 0 \downarrow_{-15V} \square_{60V} \square_{60V}$ | | 0.30 | 0.60 | μs |
| | Turn-On Time | t _{on} | | _ | 0.40 | 0.70 | |
| | Fall Time | t _f | | | 0.25 | 0.40 | |
| | Turn-Off Time | t _{off} | | - | 0.60 | 1.00 | |
| Emitter-Collector Forward Voltage | | V _{ECF} | I _{EC} = 15A, V _{GE} = 0 | - | 1.5 | 2.0 | V |
| Reverse Recovery Time | | t _{rr} | I _F = 15A, V _{GE} = 0, di / dt = -20A / μs | _ | 0.7 | 2.5 | μs |
| Thermal Resistance | | R _{th (j−c)} | IGBT | _ | — | 0.625 | °C/W |
| Thermal Resistance | | R _{th (j−c)} | Diode | _ | _ | 4.0 | °C/W |

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25

~40

1.6

 $I_{ECF} = 60A$

120

160

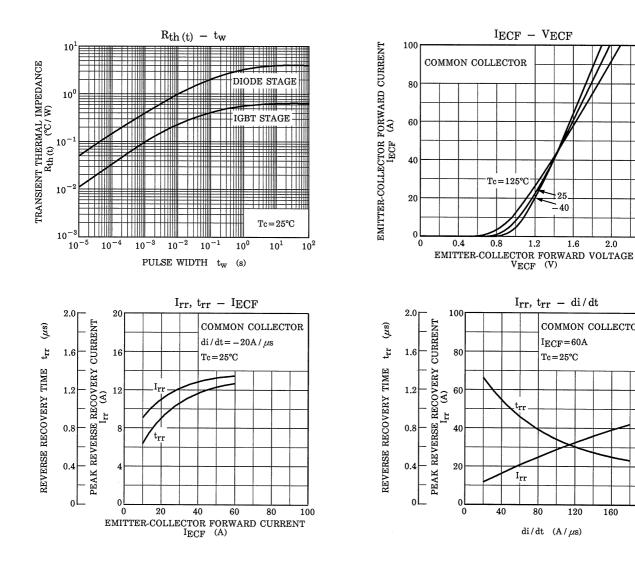
240

 $Tc = 25^{\circ}C$

2.0

COMMON COLLECTOR

2.4



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